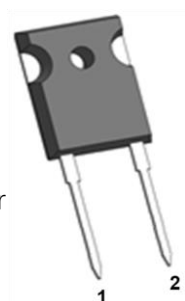


IV2D12040T2L – 1200V 40A SiC Schottky Diode

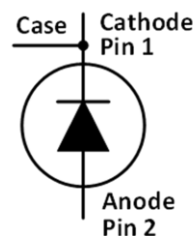
Features

- Max Junction Temperature 175°C
- High Surge Current Capacity
- Extremely Fast Reverse Recovery Time
- Reduced Losses in Associated MOSFET
- High-Frequency Operation
- Temperature Independent Switching Behavior
- Positive Temperature Coefficient on V_F
- Extremely Low V_F

Outline



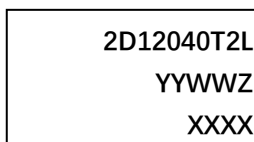
TO247-2



Applications

- EV Charger Piles
- Vienna 3-Phase PFC
- Solar Power Boost
- Inverter Free Wheeling Diodes
- Switching Mode Power Supplies

Marking Diagram



2D12040T2L = Specific Device Code
 YY = Year
 WW = Work Week
 Z = Assembly Location
 XXXX = Lot Traceability

Absolute Maximum Ratings (Tc=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{RRM}	Reverse voltage (repetitive peak)	1200	V
V_{DC}	DC blocking voltage	1200	V
I_F	Forward current (continuous) @Tc=25°C	120	A
	Forward current (continuous) @Tc=135°C	56	A
	Forward current (continuous) @Tc=151°C	40	A
I_{FSM}	Surge non-repetitive forward current sine halfwave @Tc=25°C tp=10ms	350	A
I_{FRM}	Surge repetitive forward current (Freq=0.1Hz, 100cycles) sine halfwave @Tamb=25°C tp=10ms	280	A
P_{tot}	Total power dissipation @ Tc=25°C	468	W
	Total power dissipation @ Tc=150°C	78	
$\int i^2 dt$	I^2t value @Tc=25°C tp=10ms	612.5	A ² s
Tstg	Storage temperature range	-55 to 175	°C
Tj	Operating junction temperature range	-55 to 175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.36	1.65	V	$I_F = 40 \text{ A } T_J = 25^\circ\text{C}$	Fig. 1
		1.8	2.4		$I_F = 40 \text{ A } T_J = 175^\circ\text{C}$	
I_R	Reverse Current	5	100	μA	$V_R = 1200 \text{ V } T_J = 25^\circ\text{C}$	Fig. 2
		50	1000		$V_R = 1200 \text{ V } T_J = 175^\circ\text{C}$	
C	Total Capacitance	3796		pF	$V_R = 1 \text{ V}, T_J = 25^\circ\text{C}, f = 1 \text{ MHz}$	Fig. 3
		241			$V_R = 400 \text{ V}, T_J = 25^\circ\text{C}, f = 1 \text{ MHz}$	
		171			$V_R = 800 \text{ V}, T_J = 25^\circ\text{C}, f = 1 \text{ MHz}$	
Q_c	Total Capacitive Charge	260		nC	$V_R = 800 \text{ V}, T_J = 25^\circ\text{C},$ $Q_c = \int_0^{V_R} C(V) dV$	Fig. 4
E_c	Capacitance Stored Energy	72.5		μJ	$V_R = 800 \text{ V}, T_J = 25^\circ\text{C},$ $E_c = \int_0^{V_R} C(V) \cdot V dV$	Fig. 5

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Note
$R_{th(j-c)}$	Thermal Resistance from Junction to Case	0.32	$^\circ\text{C/W}$	Fig.7

Typical Performance

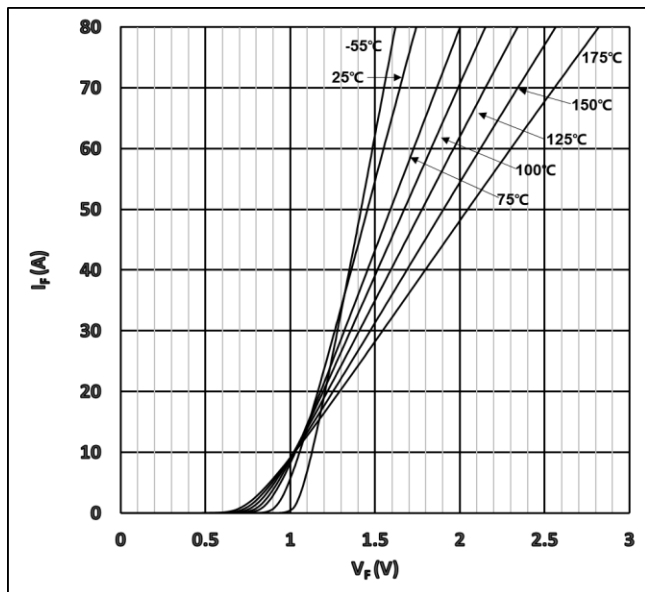


Figure 1. Typical Forward Characteristics

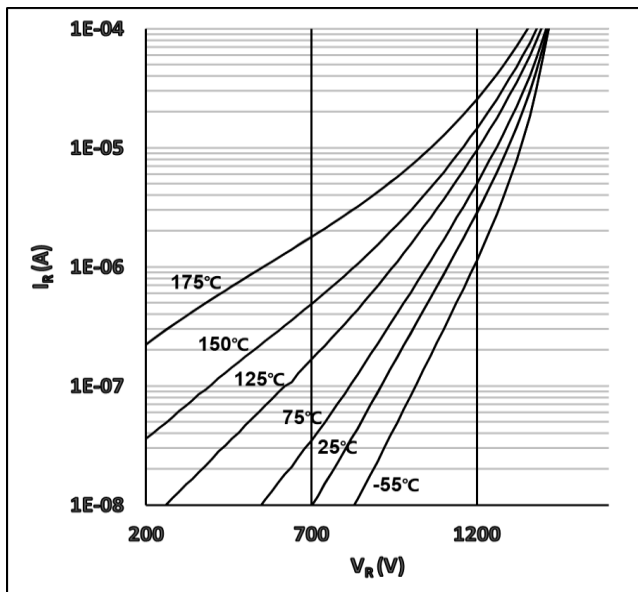


Figure 2. Typical Reverse Characteristics

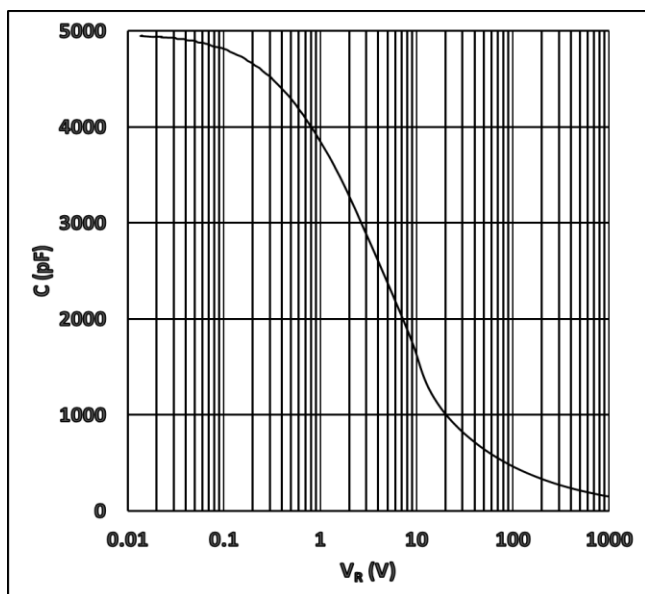


Figure 3. Capacitance vs. Reverse Voltage

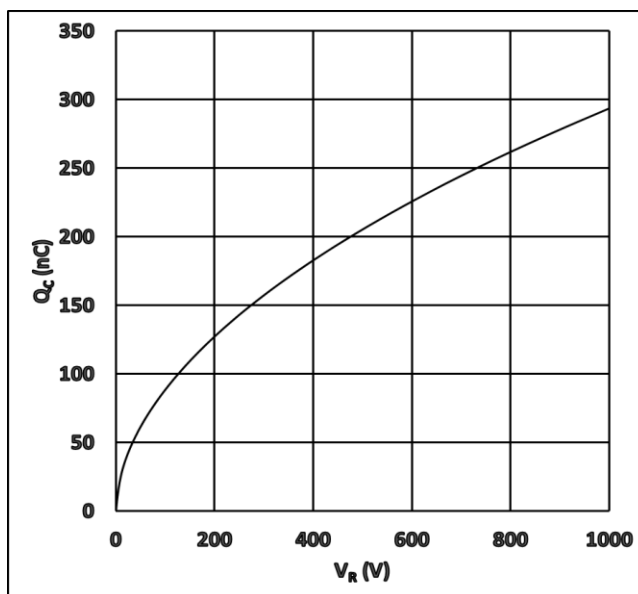


Figure 4. Recovery Charge vs. Reverse Voltage

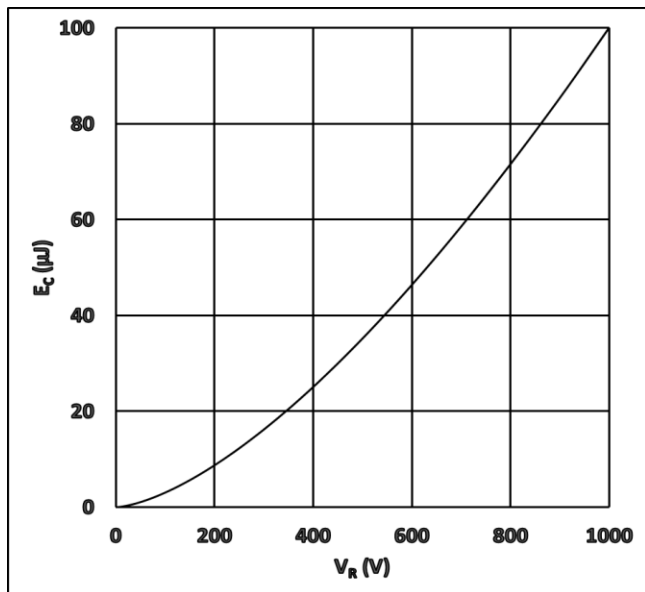


Figure 5. Capacitance Stored Energy

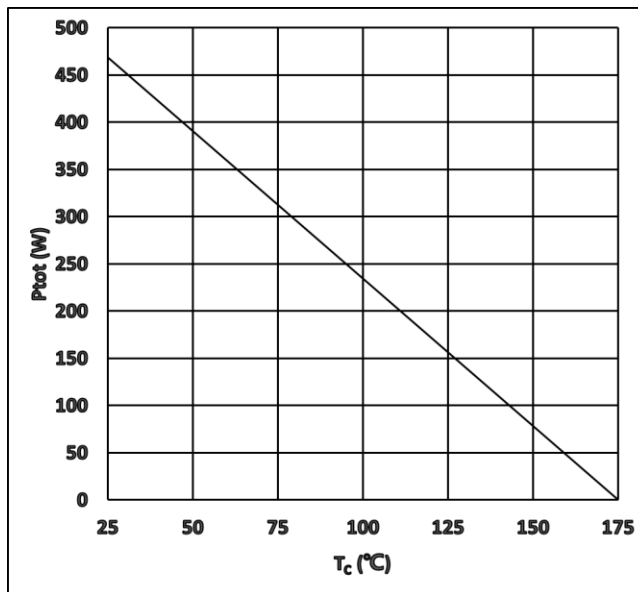


Figure 6. Power Derating

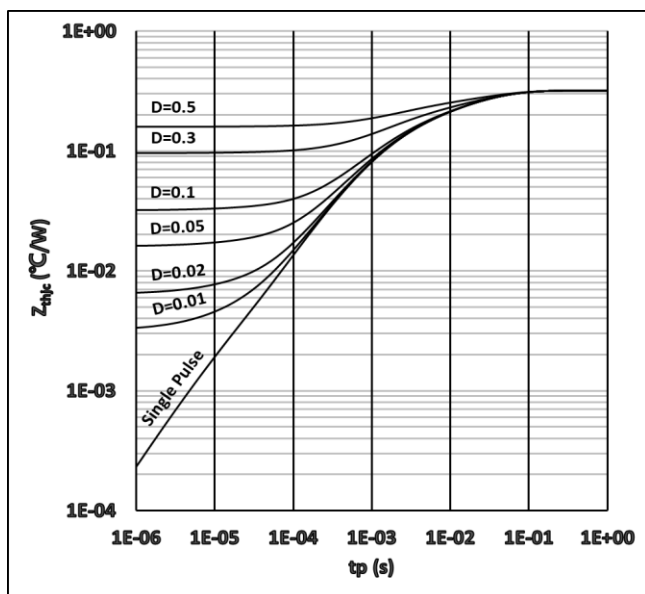


Figure 7. Transient Thermal Impedance

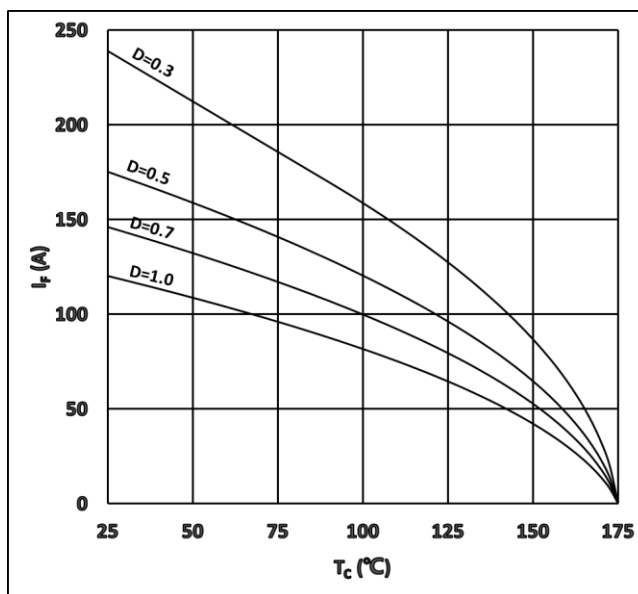
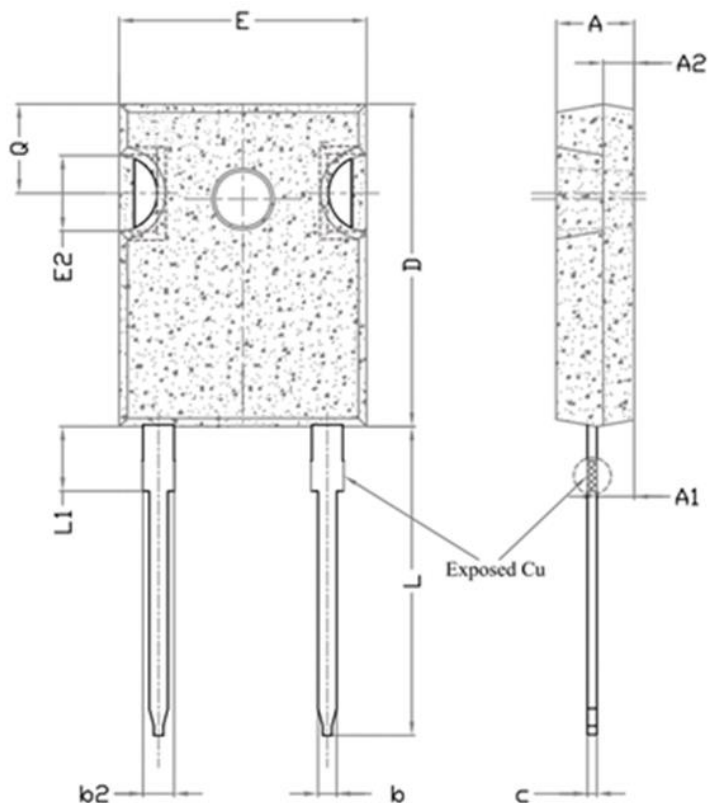
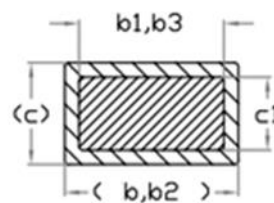
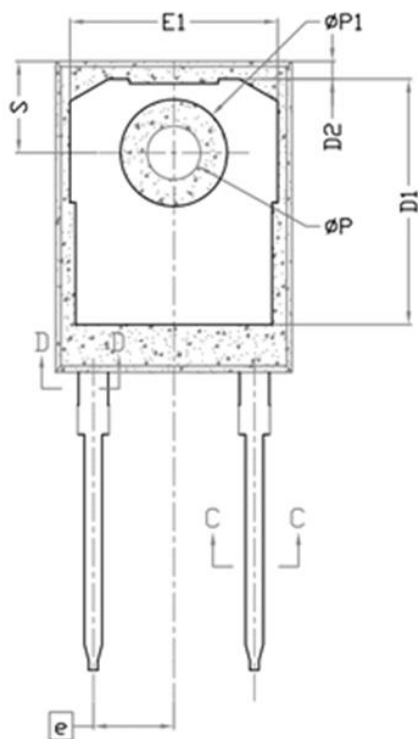


Figure 8. I_F as a Function of Temp.

Package Dimensions



Dimensions In Millimeters		
SYMBOL	MIN.	MAX.
A	4.83	5.21
A1	2.20	2.60
A2	1.50	2.49
b	1.00	1.40
b1	0.99	1.35
b2	1.80	2.41
b3	1.65	2.39
c	0.50	0.70
c1	0.38	0.70
D	20.30	21.10
D1	13.08	-
D2	0.51	1.35
E	15.45	16.13
E1	13.10	-
E2	3.68	5.49
e	5.44 BSC	
L	19.80	21.00
L1	-	4.50
φ P	3.50	3.70
φ P1	-	7.40
Q	5.39	6.20
S	6.04	6.30



Section C--C,D--D

Note:

1. Package Reference: JEDEC TO247, Variation AD
2. All Dimensions are in mm
3. Slot Required, Notch May Be Rounded or Rectangular
4. Dimension D&E Do Not Include Mold Flash
5. Subject to Change Without Notice

Notes

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